TLE2142-Q1 Excalibur™ Low-Noise High-Speed Precision Operational Amplifier

1 Features

Qualified for automotive applications

Low noise:

 10Hz: 15nV/√ Hz 1kHz: 10.5nV/√ Hz Load capability: 10000pF

Short-circuit output current: 20mA (minimum)

Slew rate: 27V/µs (minimum)

High gain-bandwidth product: 5.9MHz

Single or split supply: 4V to 44V

Fast settling time

340ns to 0.1%

400ns to 0.01%

Large output swing: V_{CC-} + 0.1V to V_{CC+} – 1V

2 Applications

Traction inverter

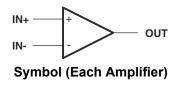
Onboard charger

Automatic transmission

DC/DC converter

3 Description

The TLE2142-Q1 device is a high-performance, internally compensated operational amplifier built



using the Texas Instruments complementary bipolar Excalibur™ process. The device is a pin-compatible upgrade to standard industry products.

The design incorporates an input stage that simultaneously achieves low audio-band noise of $10.5 \text{nV}/\sqrt{\text{Hz}}$ with a 10Hz1/f corner and symmetrical 40V/µs slew rate typically with loads up to 800pF. The resulting low distortion and high power bandwidth are important in high-fidelity audio applications. A fast settling time of 430ns to 0.1% of a 10V step with a 2kΩ/100pF load is useful in fast actuator/positioning drivers. Under similar test conditions, settling time to 0.01% is 640ns.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
TLE2142-Q1	D (SOIC, 8)	4.9mm × 6mm

- For all available packages, see Section 8.
- The package size (length × width) is a nominal value and includes pins, where applicable.

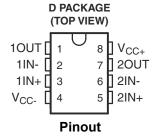




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4 Specifications

4.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		VALUE	UNIT
V _{CC+}	Supply voltage ⁽²⁾	22	V
V _{CC} -	Supply voltage	-22	V
V _{ID}	Differential input voltage ⁽³⁾	±44	V
VI	Input voltage range (any input)	V _{CC+} to (V _{CC-} – 0.3)	V
I	Input current (each input)	±1	mA
Io	Output current	±80	mA
	Total current into V _{CC+}	80	mA
	Total current out of V _{CC} -	80	mA
	Duration of short-circuit current at (or below) 25°C ⁽⁴⁾	Unlimited	
θ_{JA}	Package thermal impedance ⁽⁵⁾ (6)	97.1	°C/W
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260	°C
T _A	Operating free-air temperature range	-40 to 125	°C
T _{stg}	Storage temperature	-65 to 150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-}
- (3) Differential voltages are at IN+ with respect to IN-. Excessive current flows, if input, are brought below V_{CC} 0.3 V.
- (4) The output can be shorted to either supply. Temperature and/or supply voltages must be limited to make sure that the maximum dissipation rating is not exceeded.
- (5) Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) T_A)/θ_{JA}. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (6) The package thermal impedance is calculated in accordance with JESD 51-7.

4.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±500	\/
V (ESD)	Liectiostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±YYY	, v

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process. [Following sentences optional; see the TI Data Sheet Style Guides (STDZ017 or STDZ113).] Manufacturing with less than 500V HBM is possible with the necessary precautions. Pins listed as ±XXXV may actually have higher performance.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process. [Following sentences optional; see the TI Data Sheet Style Guides (STDZ017 or STDZ113).] Manufacturing with less than 250V CDM is possible with the necessary precautions. Pins listed as ±YYYV may actually have higher performance.

4.3 Recommended Operating Conditions

				MIN	MAX	UNIT
V _{CC±}	Supply voltage			±2	±22	V
V _{IC}	Common mode input voltage	V _{CC} = 5V		0	2.7	\/
	Common-mode input voltage $V_{CC\pm} = \pm 15V$				12.7	V
T _A	Operating free-air temperature			-40	125	°C



4.4 Thermal Information

	THERMAL METRIC(1)	D (SOIC)	- UNIT
	I DERIMAL INE I RIC		UNIT
R _{θJA}	Junction-to-ambient thermal resistance	107.4	°C/W
R _{θJC(top)} Junction-to-case (top) thermal resistance		45	°C/W
R _{θJB}	Junction-to-board thermal resistance	54.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter 4.2		°C/W
Ψ ЈВ	Junction-to-board characterization parameter		°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	_	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application

4.5 Operating Characteristics: $V_{CC} = 5V$

 V_{CC} = 5V, T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITION	NS	MIN	TYP M	AX UNIT
SR+	Positive slew rate	$A_{VD} = -1$, $R_L = 2k\Omega^{(1)}$, $C_L = 500$		45	V/µs	
SR-	Negative slew rate	$A_{VD} = -1$, $R_L = 2k\Omega^{(1)}$, $C_L = 500$	pF		42	V/µs
	Cottling time	A = 1.25\/ aton	To 0.1%		0.66	
t _s	Settling time	$A_{VD} = -1$, 2.5V step	To 0.01%		0.99	μs
.,	Faultyalant input paiga valtaga	D = 200	f = 10Hz		15	nV/√ Hz
V _n	Equivalent input noise voltage	$R_S = 20\Omega$ $f = 1kHz$		10.5		TIV/V DZ
.,	Peak-to-peak equivalent input	f = 0.1Hz to 1Hz			0.48	/
$V_{n(PP)}$	noise voltage	f = 0.1Hz to 10Hz		0.51	μV	
	Family along times of major assessment	f = 10Hz			1.92	A / -/ II=
I _n	Equivalent input noise current	f = 1kHz			0.5	— pA/√ Hz
THD+N	Total harmonic distortion plus noise	$V_{O} = 1V \text{ to } 3V, R_{L} = 2k\Omega^{(1)}, A_{VD}$	= 2, f = 10kHz	0.0	0052	%
B ₁	Unity-gain bandwidth	$R_L = 2k\Omega^{(1)}, C_L = 100pF$		5.9	MHz	
	Gain-bandwidth product	$R_L = 2k\Omega^{(1)}, C_L = 100pF, f = 100$		5.8	MHz	
вом	Maximum output-swing bandwidth ⁽²⁾	$V_{O(PP)} = 2V, R_L = 2k\Omega^{(1)}, A_{VD} = 1$		380	kHz	
φ _m	Phase margin at unity gain	$R_L = 2k\Omega^{(1)}, C_L = 100pF$			57	0

⁽¹⁾ R_L terminated at 2.5V.(2) Measured at -0.1dB.

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4.6 Operating Characteristics: $V_{CC} = \pm 15V$

 V_{CC} = ±15V, T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIO	NS	MIN	TYP	MAX	UNIT
SR+	Positive slew rate	$A_{VD} = -1$, $R_{L} = 2k\Omega$, $C_{L} = 100pF$	27 ⁽¹⁾	45		V/µs	
SR-	Negative slew rate	$A_{VD} = -1$, $R_L = 2k\Omega$, $C_L = 100 p$	F	27 ⁽¹⁾	42		V/µs
+	Sottling time	Λ = 1 10\/ stop	To 0.1%		0.43		116
lt _s	Settling time	$A_{VD} = -1$, 10V step	To 0.01%		0.64		μs
V	Equivalent input paice valtage	D = 200	f = 10Hz		15		nV/√ Hz
V _n	Equivalent input noise voltage	$R_S = 20\Omega$ $f = 1kHz$			10.5		IIV/√ ⊓∠
V	Peak-to-peak equivalent input	f = 0.1Hz to 1Hz			0.48		\/
$V_{n(PP)}$	noise voltage	f = 0.1Hz to 10Hz			0.51		μV
	Faulticology input point autrent	f = 10Hz			1.89		pA/√ Hz
I _n	Equivalent input noise current	f = 1kHz			0.47		pA/√ ⊓Z
THD+N	Total harmonic distortion plus noise	$V_{O(PP)} = 20V, R_L = 2k\Omega, A_{VD} = 1$	0, f = 10kHz		0.06		%
B ₁	Unity-gain bandwidth	$R_L = 2k\Omega$, $C_L = 100 pF$			6		MHz
	Gain-bandwidth product	$R_L = 2k\Omega$, $C_L = 100$ pF, $f = 100$ kHz			5.9		MHz
вом	Maximum output-swing bandwidth ⁽²⁾	$V_{O(PP)} = 20V, A_{VD} = 1, R_{L} = 2k\Omega$		668		kHz	
φ _m	Phase margin at unity gain	$R_L = 2k\Omega$, $C_L = 100pF$			58		٥

Specified by characterization. Measured at -0.1dB. (1) (2)



4.7 Electrical Characteristics: $V_{CC} = 5V$

 V_{CC} = 5V, at specified free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	T _A (1)	MIN	TYP	MAX	UNIT	
\/	Innut offset voltage	V = 2.5V D = 500 V = 2.5V	25°C		220	1900	\/	
V _{IO}	Input offset voltage	$V_{O} = 2.5 \text{V}, R_{S} = 50 \Omega, V_{IC} = 2.5 \text{ V}$	Full range			2600	μV	
α_{VIO}	Temperature coefficient of input offset voltage	V _O = 2.5V, R _S = 50Ω, V _{IC} = 2.5 V	Full range		1.7		μV/°C	
	line of affa at a company	V = 2.5V D = 500 V = 2.5V	25°C		8	100	Λ	
I _{IO}	Input offset current	$V_0 = 2.5V$, $R_S = 50\Omega$, $V_{IC} = 2.5 V$	Full range			200	nA	
	lamint bine arranga	V = 2.5V D = 500 V = 2.5V	25°C		-0.8	-2		
I _{IB}	Input bias current	V_{O} = 2.5V, R_{S} = 50 Ω , V_{IC} = 2.5 V	Full range			-2.3	μA	
V	Common-mode input	$R_S = 50\Omega$	25°C	0 to 3	–0.3 to 3.2		V	
V _{ICR}	voltage range	voltage range	Full range	0 to 2.7	-0.3 to 2.9		V	
		I _{OH} = -150μA		3.9	4.1			
		I _{OH} = -1.5mA	25°C	3.8	4			
.,	High-level output voltage	I _{OH} = -15mA		3.4	3.7		,,	
V_{OH}		$I_{OH} = -100 \mu A$		3.75			V	
		$I_{OH} = -1mA$	Full range	3.65				
		I _{OH} = -10mA		3.45				
	$I_{OL} = 150\mu A$ $I_{OL} = 1.5mA$			75	125	\/		
		I _{OL} = 1.5mA	I _{OL} = 1.5mA	25°C		150	225	mV
\/	Low lovel output voltage	I _{OL} = 15mA			1.2	1.4	V	
V_{OL}	Low-level output voltage	I _{OL} = 100μA				200	ma\/	
		I _{OL} = 1mA	Full range			250	mV	
		I _{OL} = 10mA				1.25	V	
۸	Large-signal differential	V = 12 5V D = 2k0 V = 4 V to 4 5 V	25°C	50	220		\//m\/	
A_{VD}	voltage amplification	V_{IC} = ±2.5V, R_L = 2k Ω , V_O = 1 V to -1.5 V	Full range	5			V/mV	
r _i	Input resistance		25°C		70		МΩ	
Ci	Input capacitance		25°C		2.5		pF	
Z _O	Open-loop output impedance	f = 1MHz	25°C		30		Ω	
OMBB	0	V V (win) B 500	25°C	85	118		-ID	
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}(min), R_S = 50\Omega$	Full range	80			dB	
l.	Supply-voltage rejection ratio	V = 10 EV/to 14EV D = 50 O	25°C	90	106		dB	
k _{SVR}	$(\Delta V_{CC\pm}/\Delta V_{IO})$			85			ub	
	Cumply ourrant	upply current $V_O = 2.5V$, No load, $V_{IC} = 2.5 V$			6.6	8.8		
I _{CC}	Supply current				,	9.2	mA	

⁽¹⁾ Full range is -40°C to 125°C.



4.8 Electrical Characteristics: $V_{CC} = \pm 15V$

 V_{CC} = ±15V, at specified free-air temperature (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	T _A ⁽¹⁾	MIN	TYP	MAX	UNIT
\/	Input offset voltage	V = 0 B = 500		25°C		290	1200	\/
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$		Full range			2000	μV
α _{VIO}	Temperature coefficient of input offset voltage	$V_{IC} = 0$, $R_S = 50\Omega$		Full range		1.7		μV/°C
l	Input offset current	$V_{IC} = 0, R_S = 50\Omega$		25°C		7	100	nA
I _{IO}	Input offset current	V _{IC} - 0, K _S - 5012		Full range			250	IIA
	Input higo ourrent			25°C		-0.7	-1.5	^
I _{IB}	Input bias current	$V_{IC} = 0$, $R_S = 50\Omega$		Full range			-1.8	μA
V	Common-mode input	D = 500		25°C	–15 to 13	–15.3 to 13.2		V
V _{ICR}	voltage range	$R_S = 50\Omega$		Full range	–15 to 12.7	–15.3 to 12.9		V
		I _O = -150μA			13.8	14.1		
	Maximum positive peak output voltage swing	$I_{O} = -1.5 \text{mA}$		25°C	13.7	14		V
.,		I _O = -15mA			13.3	13.7		
V _{OM+}		I _O = -100μA			13.7			
		I _O = -1mA		Full range	13.6			
		I _O = -10mA		13.3				
		I _O = 150μA			-14.7	-14.9		
	Maximum negative peak			25°C	-14.5	-14.8		V
\ /					-13.4	-13.8		
V_{OM-}	output voltage swing				-14.6			
				Full range	-14.5			
		I _O = 10mA			-13.4			
^	Large-signal differential	V - 140 V D - 210		25°C	100	450		\ //mm\ /
A_{VD}	voltage amplification	$V_O = \pm 10 \text{ V}, R_L = 2k\Omega$		Full range	20			V/mV
r _i	Input resistance			25°C		65		МΩ
Ci	Input capacitance			25°C		2.5		pF
Z _O	Open-loop output impedance	f = 1MHz		25°C		30		Ω
OMBB	0	V V (with) D 5	20	25°C	85	108		-ID
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}(min), R_S = 50$)()	Full range	80			dB
1.	Supply-voltage rejection ratio	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	50.0			106		
k _{SVR}	$(\Delta V_{CC\pm}/\Delta V_{IO})$	$V_{CC\pm} = \pm 2.5V \text{ to } \pm 15V, F$	$V_{CC\pm}$ = ±2.5V to ±15V, R_S = 50 Ω		85			dB
	Object described to		V _{ID} = 1 V	0500	-25	-50		
los	Short-circuit output current	$V_{O} = 0$ $V_{ID} = -1 V$		25°C	20	31		mA
	0	oly current $V_O = 0$, No load, $V_{IC} = 2.5 \text{ V}$		25°C		6.9	9	4
I _{CC}	Supply current			Full range	Full range		9.4	⊣ mA ∣

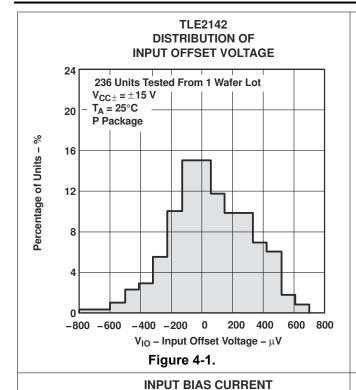
⁽¹⁾ Full range is -40°C to 125°C.

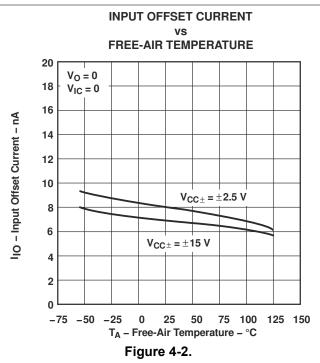


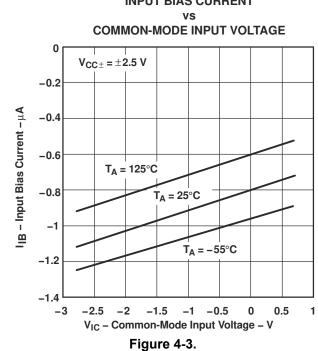
4.9 Typical Characteristics

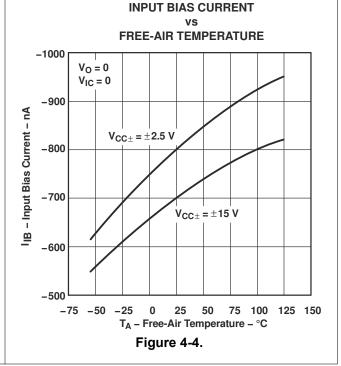
Table 4-1. Table of Graphs

I able 4-1. Table of Graphs Vision Input offset voltage						
V _{IO}	Input offset voltage		Distribution			
I _{IO}	Input offset current		vs Free-air temperature			
I _{IB}	Input bias current		vs Common-mode input voltage			
	<u> </u>		vs Free-air temperature			
		vs Supply voltage				
V _{OM+}	Maximum positive peak output voltage	a	vs Free-air temperature			
OWIT			vs Output current			
			vs Settling time			
			vs Supply voltage			
V _{OM} _	Maximum negative peak output voltag	Δ	vs Free-air temperature			
V OM-	Maximum negative peak output voltag	·	vs Output current			
V _{O(PP)}	Maximum peak-to-peak output voltage)	vs Frequency			
V _{OH}	High-level output voltage		vs Output current			
V _{OL}	Low-level output voltage		vs Output current			
	Phase shift		vs Frequency			
Δ	Large-signal differential voltage amplification		vs Frequency			
A _{VD}	Large-signal differential voltage amplif	ication	vs Free-air temperature			
Z _O	Closed-loop output impedance		vs Frequency			
I _{OS}	Short-circuit output current		vs Free-air temperature			
CMRR	Common-mode rejection ratio		vs Frequency			
CIVILLIA	Common-mode rejection ratio		vs Free-air temperature			
k	Supply-voltage rejection ratio		vs Frequency			
k _{SVR}	Supply-voltage rejection ratio		vs Free-air temperature			
	Supply ourrent		vs Supply voltage			
Icc	Supply current		vs Free-air temperature			
V _n	Equivalent input noise voltage		vs Frequency			
V _n	Input noise voltage		Over a 10-second period			
In	Noise current		vs Frequency			
THD+N	Total harmonic distortion plus noise		vs Frequency			
CD.	Clayerata		vs Free-air temperature			
SR	Slew rate		vs Load capacitance			
		Noninverting large signal	vs Time			
	Pulse response	Inverting large signal	vs Time			
		Small signal	vs Time			
B ₁	Unity-gain bandwidth	1	vs Load capacitance			
	Gain margin		vs Load capacitance			
φ _m	Phase margin		vs Load capacitance			
	-		· · ·			

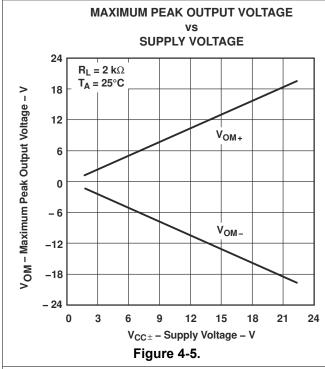


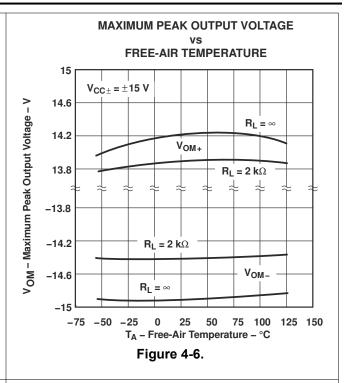


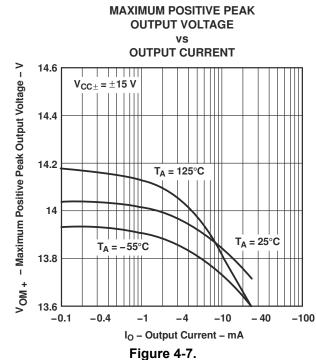


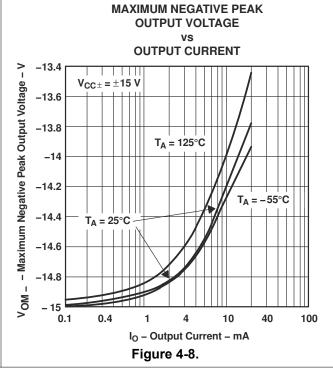


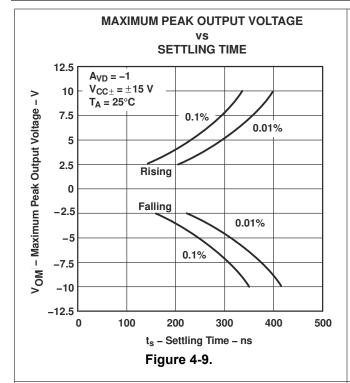


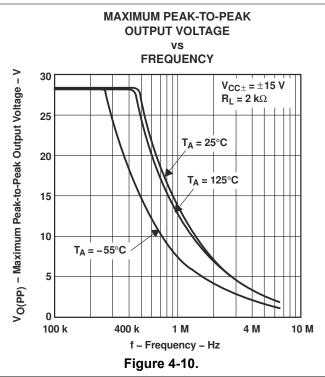


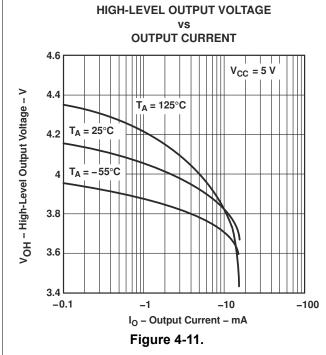


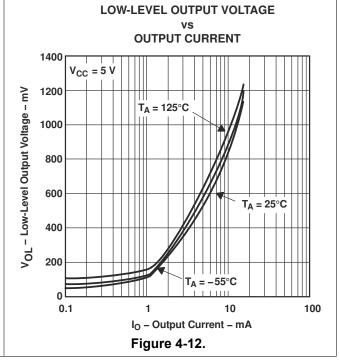




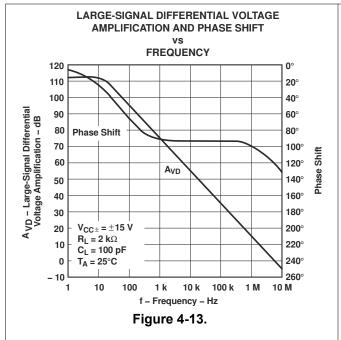


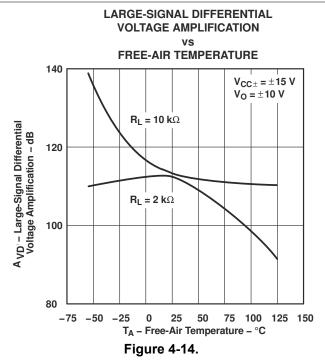


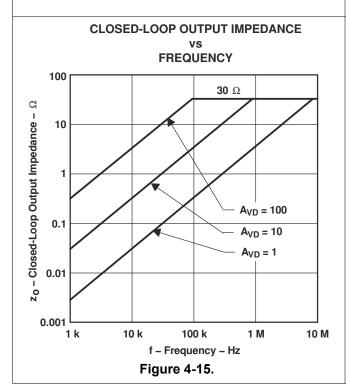


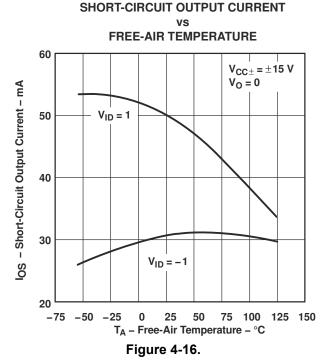












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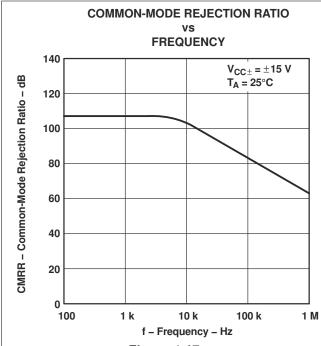
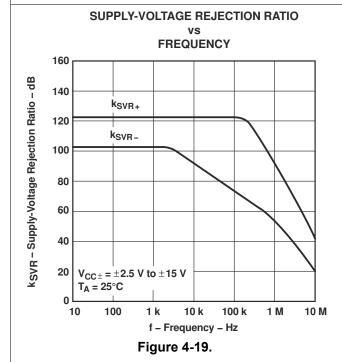
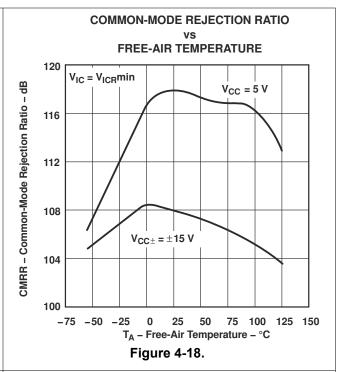
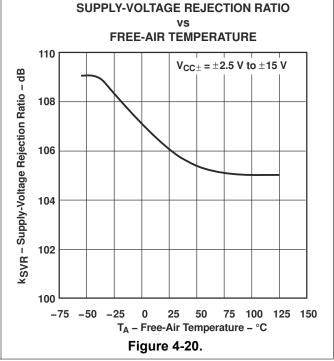


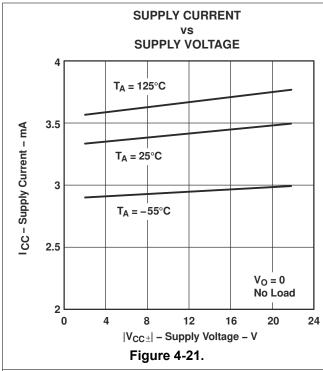
Figure 4-17.

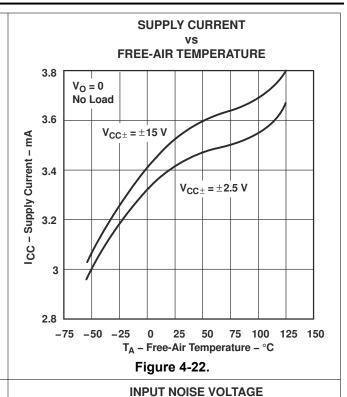


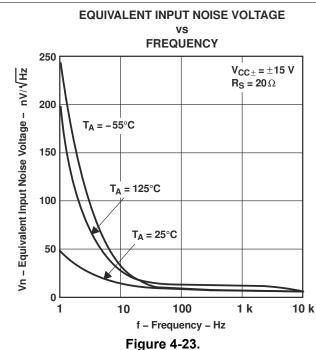


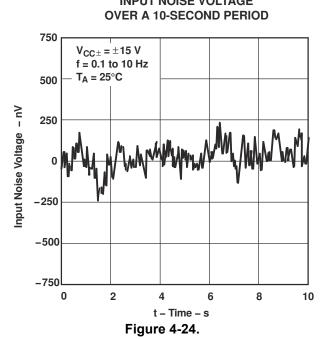


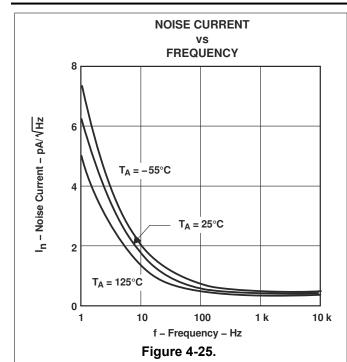


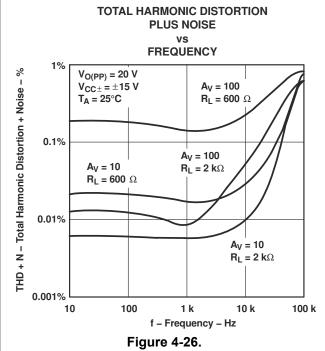


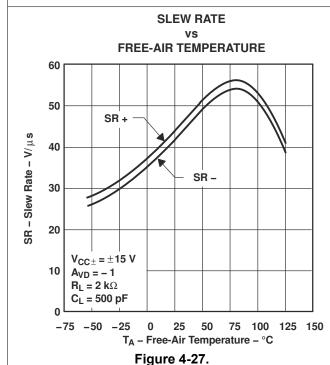


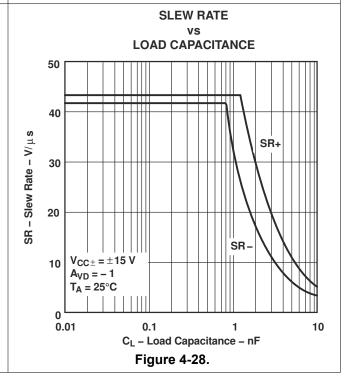




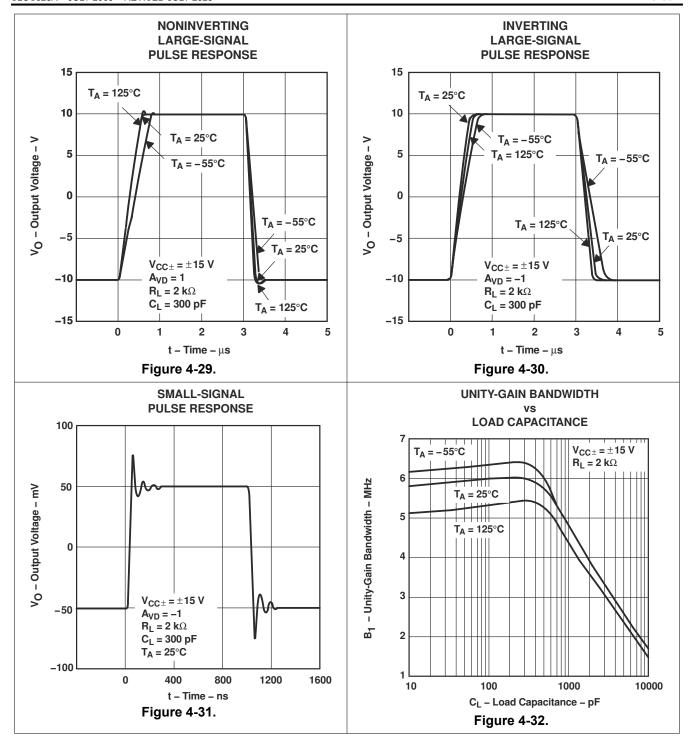




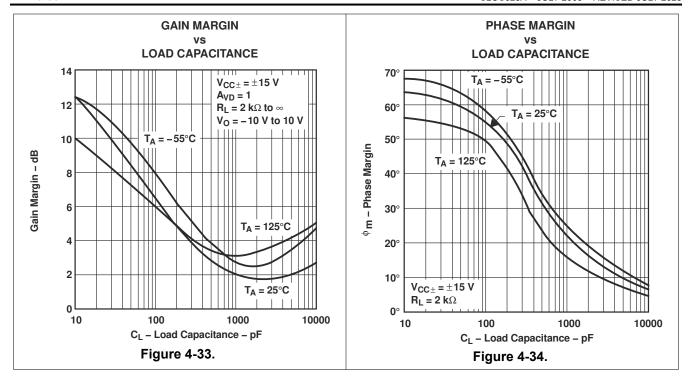








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5 Detailed Description

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

5.1 Overview

The TLE2142-Q1 is stable with capacitive loads up to 10nF, although the 6MHz bandwidth decreases to 1.8MHz at this high loading level. As such, this device is useful for low-droop sample-and-holds and direct buffering of long cables, including 4mA to 20mA current loops.

The special design also exhibits an improved insensitivity to inherent integrated circuit component mismatches as is evidenced by a $500\mu V$ maximum offset voltage and $1.7\mu V/^{\circ}C$ typical drift. Minimum common-mode rejection ratio and supply-voltage rejection ratio are 85dB and 90dB, respectively.

Device performance is relatively independent of supply voltage over the $\pm 2V$ to $\pm 22V$ range. Inputs can operate between $V_{CC-} - 0.3V$ to $V_{CC+} - 1.8V$ without inducing phase reversal, although excessive input current can flow out of each input exceeding the lower common-mode input range. The all-npn output stage provides a nearly rail-to-rail output swing of $V_{CC-} + 0.1V$ to $V_{CC+} - 1V$ under light current-loading conditions. The device can sustain shorts to either supply, because output current is internally limited, but care must be taken to make sure that maximum package power dissipation is not exceeded.

The TLE2142-Q1 can also be used as a comparator. Differential inputs of $V_{CC\pm}$ can be maintained without damage to the device. Open-loop propagation delay with TTL supply levels is typically 200ns. This gives a good indication as to output stage saturation recovery when the device is driven beyond the limits of recommended output swing.

The TLE2142-Q1 is available in an industry-standard 8-pin small-outline (D) packages. The device is characterized for operation from -40°C to 125°C.

Product Folder Links: TLE2142-Q1

6 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

6.3 Trademarks

Excalibur[™] and TI E2E[™] are trademarks of Texas Instruments. All trademarks are the property of their respective owners.

6.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

6.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

7 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

8 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TLE2142QDRQ1	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2142Q
TLE2142QDRQ1.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2142Q

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLE2142-Q1:

Catalog: TLE2142

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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Military : TLE2142M

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLE2142QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Г	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
	TLE2142QDRQ1	SOIC	D	8	2500	353.0	353.0	32.0	



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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